

U.S.S.N. 09/941,537

Abstract Amendments

Please replace the Abstract with the following replacement paragraph as follows:

0045        A method for reducing light reflectance in a photolithographic dual damascene trench patterning process ~~is disclosed~~ including providing an inter-metal dielectric (IMD) layer including at least one via opening extending through a thickness thereof; and, conformally forming an antireflectance coating (ARC) layer over ~~said~~ the IMD layer such that the ARC layer is formed over sidewalls of the at least one via opening to reduce light reflectance.